## [.WMini-Circuits

## Absorptive RF Switch with internal driver Single Supply Voltage, +2.7 V to +5.5 V

## THE BIG DEAL

- High Isolation, 69 dB at 1.0 GHz
- Low insertion loss, 0.95 dB typ. at 1 GHz
- High Input IP3, +65 dBm
- Fast switching, 300 ns typ.
- Tiny Size, $4 \times 4 \mathrm{~mm}$
- Immune to latch-up


CASE STYLE: DG983-3
Generic photo used for illustration purposes only
+RoHS Compliant
The +Suffix identifies RoHS Compliance.
See our website for methodologies and qualifications

## APPLICATIONS

- Defense
- Test and Measurements
- Switch matrices


## PRODUCT OVERVIEW

Mini-Circuits' HSWA2-63DR+ is a MMIC SPDT absorptive switch with an internal driver designed for wideband operation from 100 MHz to 6.0 GHz supporting many applications requiring high performance across a wide frequency range. This model provides excellent isolation, fast switching speed and high linearity in a tiny $4 \times 4 \mathrm{~mm} 20$-Lead MCLP package. Produced using a unique CMOS process on silicon, it offers the performance of GaAs with the advantages of conventional CMOS devices. HSWA2-63DR+ provides a high level of ESD protection and excellent repeatability.

## KEY FEATURES

| Feature |  |
| :--- | :--- |
| Wideband, 100 MHz to 6.0 GHz <br> Usable over 1 kHz to 6 GHz | Advantages |
| Absorptive switch | One model can be used in many applications, saving component count. Also ideal for wideband applications such as <br> military and instrumentation. With lower input power it can operate over 1kHz to 6 GHz covering even wider applica- <br> tions |
| High Isolation: <br> 71 dB at 1000 MHz <br> 48 dB at 6000 MHz | In the off condition, RF output ports which are not switched ON are terminated into $50 \Omega$. This enables proper imped- <br> ance termination of the circuitry following the RF output ports, preventing any unintended action such as oscillation. |
| High linearity, +65 dBm IIP3 | High isolation significantly reduces leakage of power into OFF ports. |
| Immune to Latch-up | High linearity minimizes unwanted intermodulation products which are difficult or impossible to filter in multi-carrier <br> environments such as CATV, or in the presence of strong interfering signal from adjacent circuitry or received by <br> antenna. |
| Tiny size, $4 \times 4 \mathrm{~mm}$ MCLP package | Unlike conventional CMOS devices, HSWA is immune to latch-up |
| Tiny footprint saves space in dense layouts while providing low inductance, repeatable transitions, and excellent |  |
| thermal contact to the PCB. |  |

RF ELECTRICAL SPECIFICATIONS1, 100 MHZ - 6 GHZ , TAMB $=25^{\circ} \mathrm{C}$, VDD $=+3.0 \mathrm{~V}, 50 \mathrm{OHMS}$

| Parameter | Condition (MHz) | Min. | Typ. | Max. | Units |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Frequency range |  | 100 |  | 6000 | MHz |
| Insertion loss ${ }^{2}$ | $\begin{gathered} 100-1000 \\ 1000-2000 \\ 2000-3000 \\ 3000-4000 \\ 4000-5000 \\ 5000-6000 \end{gathered}$ | $\begin{aligned} & - \\ & - \\ & - \\ & - \\ & - \end{aligned}$ | $\begin{gathered} 0.95 \\ 0.95 \\ 1.0 \\ 1.15 \\ 1.25 \\ 1.60 \end{gathered}$ | $\begin{gathered} 1.15 \\ 1.15 \\ 1.2 \\ 1.35 \\ 1.55 \\ 1.90 \end{gathered}$ | dB |
| Isolation between Common port and RF1/RF2 Ports | $\begin{gathered} 100-1000 \\ 1000-2000 \\ 2000-3000 \\ 3000-4000 \\ 4000-5000 \\ 5000-6000 \end{gathered}$ | $\begin{aligned} & 69 \\ & 65 \\ & 63 \\ & 62 \\ & 52 \\ & 44 \end{aligned}$ | $\begin{aligned} & 71 \\ & 67 \\ & 68 \\ & 67 \\ & 57 \\ & 48 \end{aligned}$ | $\begin{aligned} & - \\ & - \\ & - \\ & - \\ & - \end{aligned}$ | dB |
| Isolation between RF1 and RF2 Ports | $\begin{gathered} 100-1000 \\ 1000-2000 \\ 2000-3000 \\ 3000-4000 \\ 4000-5000 \\ 5000-6000 \end{gathered}$ | $\begin{aligned} & 67 \\ & 63 \\ & 59 \\ & 60 \\ & 54 \\ & 44 \end{aligned}$ | 69 <br> 64 <br> 62 <br> 64 <br> 60 <br> 50 | $\begin{aligned} & - \\ & - \\ & - \\ & - \end{aligned}$ | dB |
| Return loss (All Ports) | $\begin{gathered} 100-4000 \\ 4000-5000 \\ 5000-6000 \end{gathered}$ | $\begin{aligned} & - \\ & - \\ & - \end{aligned}$ | $\begin{aligned} & 20 \\ & 15 \\ & 13 \end{aligned}$ | $-$ | dB |
| Input IP2 | 100-6000 | - | 110 | - | dBm |
| Input IP3 | 100-6000 | 60 | 65 | - | dBm |
| 1.0 dB Input compression ${ }^{3}$ | 100-6000 | 33 | 35 | - | dBm |
| Thermal Resistance, junction-to-ambient |  |  | 78 |  | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

DC ELECTRICAL SPECIFICATIONS

| Parameter | Min. | Typ. | Max. | Units |
| :--- | :---: | :---: | :---: | :---: |
| Supply voltage, $\mathrm{V}_{\mathrm{DD}}$ | 2.7 |  | 5.5 | V |
| Supply current |  | 120 | 200 | $\mu \mathrm{~A}$ |
| Control voltage Low | -0.3 |  | 0.6 | V |
| Control voltage High | 1.17 |  | 3.6 | V |
| Control current |  | 9 | 12 | $\mu \mathrm{~A}$ |

## Notes:

1. Tested on Mini-Circuits' test board TB-919+, using Agilent's N5230A
network analyzer (see Characterization test circuit, Fig.2).
2. Insertion loss values are de-embedded from test board loss.
3. Do not exceed RF input power as shown in Absolute Maximum Ratings table.

## SWITCHING SPECIFICATIONS

| Parameter | Condition | Min. | Typ. | Max. | Units |
| :--- | :---: | :---: | :---: | :---: | :---: |
| Switching time <br> $50 \%$ control to 90/10\%RF | fctrl=1KHz <br> VDD $=3 \mathrm{~V}$ <br> Vctrl High=1.8V <br> Vctrl Low=0V |  | 300 | 400 | nS |
|  | Video feed-through |  | 27 |  | $\mathrm{mV}_{\text {p.p }}$ |
|  |  |  | 67 |  | nS |
| Rise/Fall time <br> 10 to $90 \%$ or 90 to $10 \%$ |  |  |  |  |  |

## MAXIMUM RATINGS ${ }^{4}$

| Parameter | Ratings |
| :--- | :---: |
| Operating temperature | $-40^{\circ} \mathrm{C}$ to $+105^{\circ} \mathrm{C}$ |
| Storage temperature | $-65^{\circ} \mathrm{C}$ to $150^{\circ} \mathrm{C}$ |
| $\mathrm{V}_{\text {DD }}$, Supply voltage | -0.3 to 5.5 V |
| Voltage control | -0.3 V Min. 3.6 Max. |
| RF Input power, $\mathrm{CW}^{5}$ | +30 dBm |
| RF Power into output ports ${ }^{5}$ | +20 dBm |
| Maximum Die Junction Temperature | $150^{\circ} \mathrm{C}$ |

4. Operation of this device above any of these conditions may cause permanent damage.
5. 100\% Duty Cycle, all band, $50 \Omega$

TRUTH TABLE

| Mode | State of Control Voltage <br> Control 1 |  |
| :---: | :---: | :---: |
| RF COM-RF1 ON | HIGH | LOW |
| RF COM-RF2 ON | LOW | HIGH |
| ALL OFF | LOW | LOW |
| Unsupported | HIGH | HIGH |

MMIC

## SP2T RF Switch

HSWA2-63DR+

## Absorptive RF Switch with internal driver

Single Supply Voltage, +2.7 V to +5.5 V


| Function | Pad <br> Number | Description |
| :---: | :---: | :---: |
| RF COM | 8 | RF Common/ SUM port* |
| RF1 | 3 | RF out \#1/In port \#1* |
| RF2 | 13 | RF out \#1/In port \#2* |
| Control 1 | 17 | CMOS Control IN \#1 |
| Control 2 | 16 | CMOS Control IN \#2 |
| VDD | 20 | Supply voltage |
| GND | $1,2,4,7,9,10-12$, <br> $14,15,18,19$ | Ground |

* Must be held at OVDC. If required add DC blocking capacitors on these ports.


## CHARACTERIZATION \& APPLICATION CIRCUIT



Figure 2. Block Diagram of test Circuit used for characterization
(DUT soldered on Mini-Circuits' TB-919+)
Note: Cblock is required only when DC is present on RF ports.

PRODUCT MARKING
H63DR

| Performance Data | Data Table |
| :--- | :--- |
| Swept Graphs |  |, | DG983-3 Plastic package, exposed paddle, termination finish=NiPdAu |
| :--- |
| Case Style |
| Tape \& Reel <br> Standard quantities available on reel |
| Suggested Layout for PCB Design |
| Evaluation Board |
| Environmental Ratings |

## ESD RATING

Human Body Model (HBM): Class 2 (Pass 2000V) in accordance with MIL-STD-883, Method 3015

## MSL RATING

Moisture Sensitivity: MSL3 in accordance with IPC/JEDEC J-STD-O20D

## MSL TEST FLOW CHART



## NOTES

A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.



